IN-F22IR

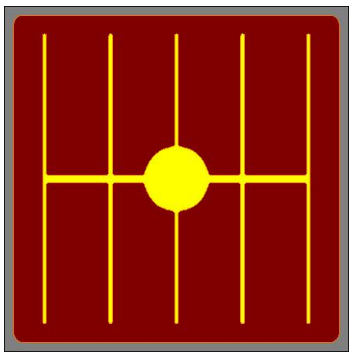
DRAFT

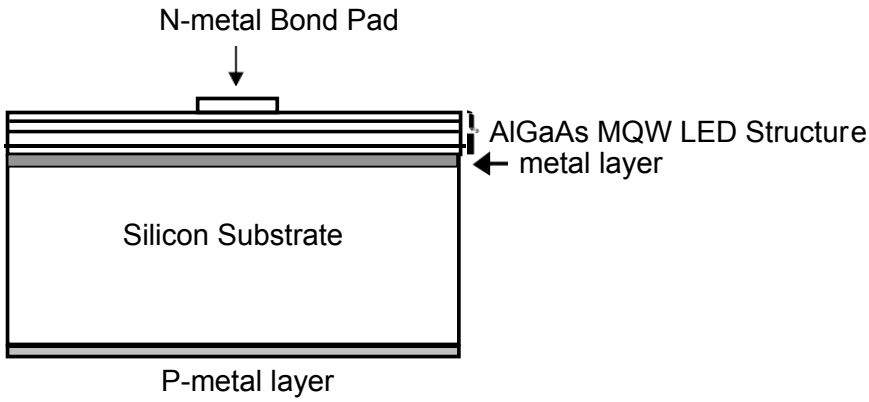
Chip characteristics:

- **Chip size:** 560±25 μm × 560±25 μm
- **Chip thickness:** 180±25 μm
- **N-bonding pad:**105±15μm
- **Conductive Si-substrate**
- **Rough Surface**

Descriptions:

F22IR is a Infra-red LED chip made from MOCVD process and bonded with Silicon. It is fabricated by the HPO ' s proprietary metal Bonding mechanism, F22IR is featured by homogeneous and high light output at top side with superior beam pattern. Excellent performance under sunlight and reliable life-long stability make F22IR ideal for IrDA, Encoder, data communication applications.





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Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{F1}	1.6	-	1.8	V	I_F=500 mA
Threshold voltage	V_{F3}	1.0	-	1.3	V	I_F=10 μA
Reverse Current	I_R	-	-	10.0	μA	V_R=5 V
Peak wavelength	λp	800	-	900	nm	I_F=500 mA
Spectral Line Half Width	△λ	-	30	-	nm	I_F=500 mA
Radiant Power	Po	120	-	-	mW	I_F=500 mA

*Po is measured on chip form with HPO's tester.

Ver: 01-Feb/19/2020